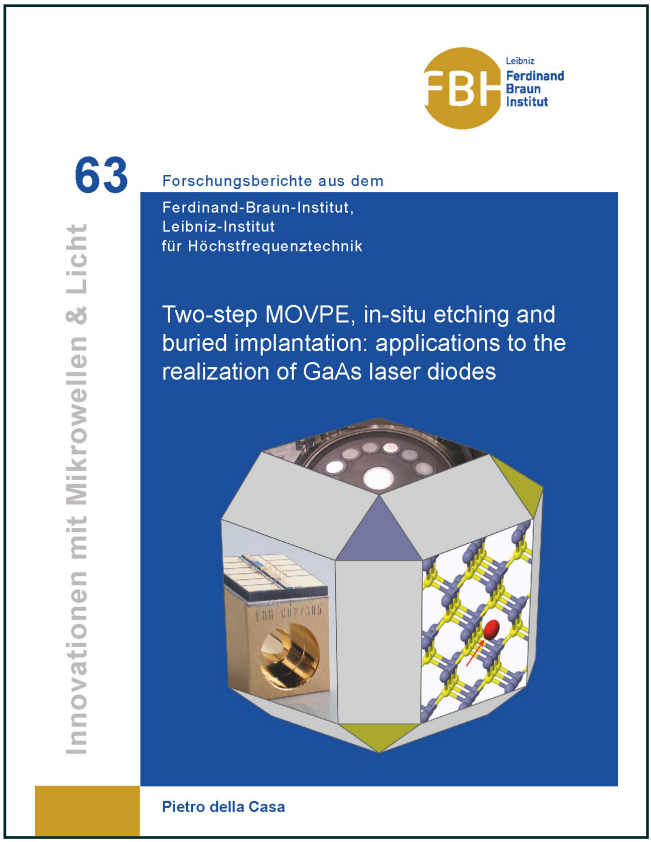
Pietro della Casa (Autor)

# Two-step MOVPE, in-situ etching and buried implantation: applications to the realization of GaAs laser diodes

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